

Bragg's Law	Inter-planar Spacing	Hydrogen Like Spectra (R = $1.097 \times 10^7 \text{ m}^{-1}$ )
$2d_{hkl} \sin\theta = n\lambda$	$d_{hkl} = \frac{a}{\sqrt{h^2 + k^2 + l^2}}$	$\frac{1}{\lambda} = RZ^2 \left( \frac{1}{n_f^2} - \frac{1}{n_i^2} \right)$

1. The  $2\theta$  values in degrees for first order diffraction peaks are given below for a metal with cubic structure, using X-rays from Cu-K $\alpha$  radiation ( $Z = 29$ ): 36.3, 42.2, 61.6, 73.6.

(a) Determine the wavelength of the X-rays used.

$$\frac{1}{\lambda} = RZ^2 \left( \frac{1}{n_f^2} - \frac{1}{n_i^2} \right)$$

$$\frac{1}{\lambda} = 1.097 \times 10^7 \times (29-1)^2 \left( \frac{1}{1^2} - \frac{1}{2^2} \right) = 1.097 \times 10^7 \times 28^2 \times \frac{3}{4}$$

$$\frac{1}{\lambda} = 6.45 \times 10^9 \text{ m}^{-1} \Rightarrow \lambda = 1.55 \times 10^{-10} \text{ m} = \underline{\underline{0.155 \text{ nm}}}$$

(b) Derive an expression for  $\frac{\sin^2\theta}{h^2+k^2+l^2}$ .

$$2d_{hkl} \sin\theta = n\lambda$$

$$2 \cdot \frac{a}{\sqrt{h^2+k^2+l^2}} \cdot \sin\theta = \lambda \Rightarrow \frac{4a^2 \sin^2\theta}{(h^2+k^2+l^2)} = \lambda^2$$

$$\frac{\sin^2\theta}{(h^2+k^2+l^2)} = \frac{\lambda^2}{4a^2}$$

(c) Complete the table below.

$2\theta$ (deg.)	$\theta$	$\sin^2\theta$	Normalize	Clear Fractions	$h^2+k^2+l^2$	(hkl)	$\frac{\sin^2\theta}{h^2+k^2+l^2}$
36.3	18.15	0.09704	1	3	3	111	0.03235
42.2	21.1	0.1296	1.33	4	4	200	0.0324
61.6	30.8	0.2622	2.70	8	8	220	0.0328
73.6	36.8	0.3588	3.697	11	11	311	0.0326

(d) Determine the crystal structure. FCC, since  $(hkl) \rightarrow$  odd or even Ave = 0.0325

(e) Determine the lattice constant.

(f) Determine the atomic radius.

$$(e) \frac{\lambda^2}{4a^2} = 0.0325 \Rightarrow a^2 = \frac{\lambda^2}{4 \times 0.0325} \Rightarrow a = \sqrt{\frac{0.155^2}{4 \times 0.0325}}$$

$$a = 0.430 \text{ nm}$$

$$(f) \sqrt{2}a = 4R$$

$$R = \frac{\sqrt{2}a}{4} = \frac{\sqrt{2} \times 0.430}{4} = 0.152 \text{ nm}$$

$\rho_{ave} = \frac{100}{\frac{C_1}{\rho_1} + \frac{C_2}{\rho_2}}$	$A_{ave} = \frac{100}{\frac{C_1}{A_1} + \frac{C_2}{A_2}}$	
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2. Calculate the unit cell edge length for an 85 wt% Fe-15 wt% V alloy. All of the vanadium is in solid solution, and, at room temperature the crystal structure for this alloy is BCC. The room-temperature density of Fe is  $7.87 \text{ g/cm}^3$ , and its atomic weight is  $55.85 \text{ g/mol}$ . The room-temperature density of V is  $6.10 \text{ g/cm}^3$ , and its atomic weight is  $50.94 \text{ g/mol}$ .

$$\rho_{ave} = \frac{100}{\frac{85}{7.87} + \frac{15}{6.10}} = 7.54 \text{ g/cm}^3$$

$$A_{ave} = \frac{100}{\frac{85}{55.85} + \frac{15}{50.94}} = 55.05 \text{ g/mol}$$

$$\rho = \frac{M}{V} \Rightarrow V = \frac{M}{\rho} = a^3 \Rightarrow a = \sqrt[3]{\frac{2 \times 55.05}{6.022 \times 10^{23}}} = (2.42 \times 10^{-8} \text{ cm}^3)^{\frac{1}{3}} = 2.42 \times 10^{-8} \text{ cm}$$

$$a = 0.289 \text{ nm}$$

$$a = 2.89 \times 10^{-8} \text{ cm}$$

$$a = 0.289 \times 10^{-7} \text{ cm}$$

3. Compute the radius  $r$  of an impurity atom that just fits into a BCC tetrahedral interstitial site in terms of the atomic radius  $R$  of the host atom (without introducing lattice strains).

$$(R+r)^2 = \left(\frac{1}{2}a\right)^2 + \left(\frac{1}{4}a\right)^2$$

$$= \frac{a^2}{4} + \frac{a^2}{16}$$

$$(R+r)^2 = \frac{5a^2}{16}$$

$$(R+r)^2 = \frac{5}{16} \times \frac{16R^2}{3}$$

$$R+r = \sqrt{\frac{5}{3}} \cdot R = 1.291R$$

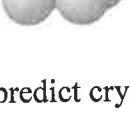
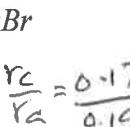
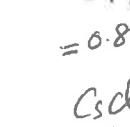
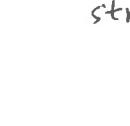
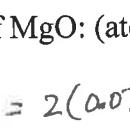
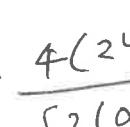
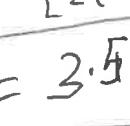
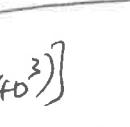
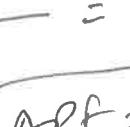
$$r = 0.291R$$

$$(b)$$

$$a = \frac{4R}{\sqrt{3}}$$

$$a = \frac{16R}{3}$$

**Table 12.3 Ionic Radii for Several Cations and Anions  
(for a Coordination Number of 6)**

Cation	Ionic Radius (nm)	Anion	Ionic Radius (nm)	$\frac{r_{\text{cation}}}{r_{\text{anion}}}$	
$\text{Al}^{3+}$	0.053	$\text{Br}^-$	0.196	0.225-0.414	
$\text{Ba}^{2+}$	0.136	$\text{Cl}^-$	0.181		
$\text{Ca}^{2+}$	0.100	$\text{F}^-$	0.133		
$\text{Cs}^+$	0.170	$\text{I}^-$	0.220		
$\text{Fe}^{2+}$	0.077	$\text{O}^{2-}$	0.140		
$\text{Fe}^{3+}$	0.069	$\text{S}^{2-}$	0.184		
$\text{K}^+$	0.138				
$\text{Mg}^{2+}$	0.072				
$\text{Mn}^{2+}$	0.067				
$\text{Na}^+$	0.102				
$\text{Ni}^{2+}$	0.069				
$\text{Si}^{4+}$	0.040				
$\text{Ti}^{4+}$	0.061				

4. On the basis of ionic charge and ionic radii given, predict crystal structures for the following materials: (a)  $\text{CaO}$       (b)  $\text{MnS}$       (c)  $\text{CsBr}$       (d)  $\text{MgO}$

$$\frac{r_c}{r_a} = \frac{0.1}{0.14} = 0.714$$

Nacl struc

$$\frac{r_c}{r_a} = \frac{0.067}{0.184} = 0.364$$

ZnS struc

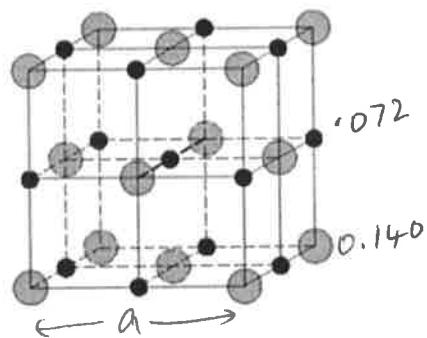
$$\frac{r_c}{r_a} = \frac{0.170}{0.196} = 0.867$$

CsCl struc

$$\frac{r_c}{r_a} = \frac{0.072}{0.140} = 0.514$$

Nacl struc

5. Determine the density and atomic packing factor of  $\text{MgO}$ : (atomic masses, Mg = 24.3 and O = 16.0)



$$a = 2r + 2R = 2(0.072 + 0.140)$$

$$\rho = \frac{M}{V} = \frac{4(24.3 + 16)/6.02 \times 10^{23}}{[2(0.072 + 0.140)]^3 \times 10^{-21}} \text{ g/cm}^3$$

$$\rho = 3.51 \text{ g/cm}^3$$

$$\text{APF} = \frac{4 \left[ \frac{4}{3} \pi (0.072)^3 + \frac{4}{3} \pi (0.140)^3 \right]}{[2(0.072 + 0.140)]^3} = \frac{0.05223}{0.0762} = 0.69$$

$$\text{APF} = 0.69$$

$$\sigma = n|e|\mu_e + p|e|\mu_h$$

6. The following electrical characteristics have been determined for both intrinsic and p-type extrinsic gallium antimonide (GaSb) at room temperature:

	$\sigma (\Omega \cdot m)^{-1}$	$n (m^{-3})$	$p (m^{-3})$
Intrinsic	$8.9 \times 10^4$	$8.7 \times 10^{23}$	$8.7 \times 10^{23}$
Extrinsic (p-type)	$2.3 \times 10^5$	$7.6 \times 10^{22}$	$1.0 \times 10^{25}$

Calculate electron and hole mobilities.

$$8.9 \times 10^4 = 1.6 \times 10^{-19} (8.7 \times 10^{23}) (\mu_e + \mu_h)$$

$$8.9 \times 10^4 = \mu_e + \mu_h = 0.6394$$

$$\frac{1.6 \times 10^{-19} \times 8.7 \times 10^{23}}{8.9 \times 10^4}$$

$$2.3 \times 10^5 = 1.0 \times 10^{-19} \times 1.6 \times 10^{25} \times \mu_h$$

$$\begin{aligned} \frac{2.3 \times 10^5}{1.6 \times 10^6} &= \mu_h = 0.14 \\ &\boxed{\mu_h = 0.14} \\ &\boxed{\mu_e = 0.49} \end{aligned}$$

7. Germanium to which  $5 \times 10^{22} m^{-3}$  Sb atoms have been added is an extrinsic semiconductor at room temperature, and virtually all the Sb atoms may be thought of as being ionized (i.e., one charge carrier exists for each Sb atom).  $\uparrow$  Valence

(a) Is this material n-type or p-type?

(b) Calculate the electrical conductivity of this material, assuming electron and hole mobilities of 0.1 and 0.05  $m^2/V \cdot s$ , respectively.

$G = ne\mu_e$ , extrinsic, electrons are dominant carriers.

$$G = 5 \times 10^{22} \times 1.6 \times 10^{-19} \times 0.1 \quad \# \text{ of holes are negligible.}$$

$$\boxed{G = 800 (\Omega \cdot m)^{-1}}$$